

REF50xxA-Q1 Low-Noise, Very Low Drift, Precision Voltage Reference

1 Features

- Qualified for Automotive Applications
- Low Temperature Drift
 - Standard Grade: 8 ppm/°C (max)
- High Accuracy
 - Standard Grade: 0.1% (max)
- Low Noise: 3 $\mu\text{V}_{\text{PP}}/\text{V}$
- Excellent Long-Term Stability:
 - 5 ppm/1000 hr (typ) after 1000 hours
- High Output Current: ± 10 mA
- Temperature Range: -40°C to 125°C

2 Applications

- 16-Bit Data Acquisition Systems
- ATE Equipment
- Industrial Process Control
- Medical Instrumentation
- Optical Control Systems
- Precision Instrumentation

3 Description

The REF50xxA-Q1 family of devices is low-noise, low-drift, very-high precision-voltage reference. These reference devices are capable of both sinking and sourcing, and are very robust with regard to line and load changes.

Excellent temperature drift (3 ppm/°C) and high accuracy (0.05%) are achieved using proprietary design techniques. These features combined with very low noise make the REF50xxA-Q1 family of devices ideal for use in high-precision data acquisition systems.

Each reference voltage is available in a standard-grade versions. The devices are offered in SO-8 packages and are specified from -40°C to 125°C .

Device Information(1)

PART NUMBER	PACKAGE	OUTPUT VOLTAGE
REF5020A-Q1	SOIC (8)	2.048 V
REF5025A-Q1		2.5 V
REF5030A-Q1		3 V
REF5040A-Q1		4.096 V
REF5045A-Q1		4.5 V
REF5050A-Q1		5 V

(1) For all available packages, see the orderable addendum at the end of the data sheet.

4 Simplified Schematic

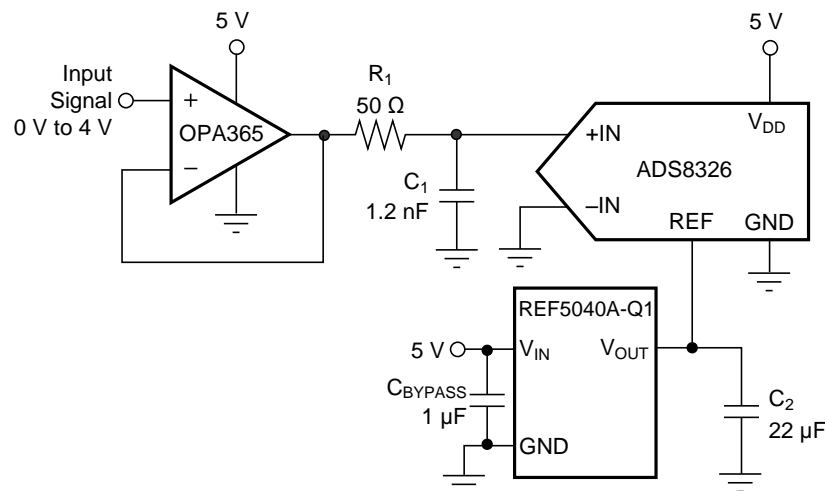


Table of Contents

1 Features	1	8.3 Feature Description	11
2 Applications	1	8.4 Device Functional Modes	12
3 Description	1	9 Application and Implementation	13
4 Simplified Schematic	1	9.1 Application Information	13
5 Revision History	2	9.2 Typical Applications	13
6 Pin Configuration and Functions	4	10 Power Supply Recommendations	16
7 Specifications	4	11 Layout	16
7.1 Absolute Maximum Ratings	4	11.1 Layout Guidelines	16
7.2 ESD Ratings	4	11.2 Layout Example	16
7.3 Recommended Operating Conditions	5	12 Device and Documentation Support	17
7.4 Thermal Information	5	12.1 Documentation Support	17
7.5 Electrical Characteristics: Per Device	5	12.2 Related Links	17
7.6 Electrical Characteristics: All Devices	6	12.3 Trademarks	17
7.7 Typical Characteristics	7	12.4 Electrostatic Discharge Caution	17
8 Detailed Description	11	12.5 Glossary	17
8.1 Overview	11	13 Mechanical, Packaging, and Orderable Information	18
8.2 Functional Block Diagram	11		

5 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

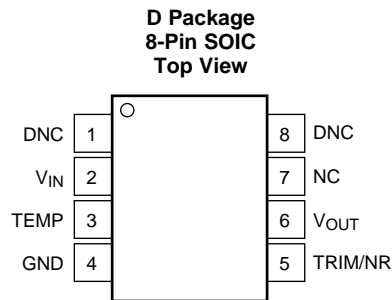
Changes from Revision G (October 2013) to Revision H	Page
• Added the <i>Pin Configuration and Functions</i> section, <i>Recommended Operating Conditions</i> table, <i>Thermal Information</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> section, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section	1
• Added A-Q1 to the end of the device numbers	1
• Changed the MIN and MAX values for the REF5040 initial accuracy parameter in the <i>Electrical Characteristics</i> table	5

Changes from Revision F (September 2011) to Revision G	Page
• Deleted reference to <i>high grade</i> throughout the document	1
• Deleted <i>Package/Ordering Information</i> table from datasheet	4
• Deleted references to the MSOP-8 package and <i>High-Grade</i> from the <i>THERMAL HYSTERESIS</i> section of the <i>ELECTRICAL CHARACTERISTICS: ALL DEVICES</i> table	6
• Deleted references to the MSOP-8 package from the <i>LONG-TERM STABILITY</i> section of the <i>ELECTRICAL CHARACTERISTICS: ALL DEVICES</i> table	6
• Deleted graphs for MSOP-8 package from <i>TYPICAL CHARACTERISTICS</i> section	9

Changes from Revision E (August 2011) to Revision F	Page
• Added REF5045AQDRQ1 HBM ESD rating of 1000 V	4

Changes from Revision D (October, 2010) to Revision E	Page
• Added <i>Thermal Hysteresis</i> parameters and specifications	6
• Added <i>Long-Term Stability</i> parameters and specifications	6
• Added Figure 22 through Figure 24	9
• Added <i>Thermal Hysteresis</i> section.....	13
• Revised <i>Noise Performance</i> section; added paragraph with links to applications articles	14

6 Pin Configuration and Functions



DNC = Do not connect

NC = No internal connection

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
DNC	1	—	Do not connect. Do not use.
	8		
GND	4	—	Ground
NC	7	—	No internal connection. Do not use.
TEMP	3	O	Temperature-dependent voltage output
TRIM/NR	5	I	Trim and noise reduction for ± 15 -mV output adjustment
V_{IN}	2	I	Input supply voltage
V_{OUT}	6	O	Reference voltage output

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

	MIN	MAX	UNIT
Input voltage		18	V
Output short-circuit		30	mA
Operating temperature	–40	125	°C
Junction temperature (T_J max)		150	°C
Storage temperature (T_{stg})	–65	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

7.2 ESD Ratings

		VALUE	UNIT
REF5020A-Q1, REF5040A-Q1, AND REF5050A-Q1			
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	± 500	V
	Charged-device model (CDM), per AEC Q100-011	± 1000	
	Machine Model (MM)	200	
REF5030A-Q1 AND REF5045A-Q1			
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	± 1000	V
	Charged-device model (CDM), per AEC Q100-011	± 1000	
	Machine Model (MM)	200	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
V_{IN} Supply input voltage	$V_{OUT} + 0.2^{(1)}$	18	V

(1) For $V_{OUT} \leq 2.5$ V, the minimum supply voltage is 2.7 V.

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		D (SOIC) 8 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	107.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	48.8	
$R_{\theta JB}$	Junction-to-board thermal resistance	48.3	
Ψ_{JT}	Junction-to-top characterization parameter	6.8	
Ψ_{JB}	Junction-to-board characterization parameter	47.6	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Electrical Characteristics: Per Device

$T_A = 25^\circ\text{C}$, $I_{LOAD} = 0$, $C_L = 1 \mu\text{F}$, $V_{IN} = (V_{OUT} + 0.2 \text{ V})$ to 18 V (unless otherwise noted).

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
REF5020 ($V_{OUT} = 2.048 \text{ V}$)⁽¹⁾					
V_{OUT} Output voltage	$2.7 \text{ V} < V_{IN} < 18 \text{ V}$		2.048		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output voltage noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		6		μV_{PP}
REF5025 ($V_{OUT} = 2.5 \text{ V}$)					
V_{OUT} Output voltage			2.5		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output Voltage Noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		7.5		μV_{PP}
REF5030 ($V_{OUT} = 3 \text{ V}$)					
V_{OUT} Output voltage			3		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output voltage noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		9		μV_{PP}
REF5040 ($V_{OUT} = 4.096 \text{ V}$)					
V_{OUT} Output voltage			4.096		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output voltage noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		12		μV_{PP}
REF5045 ($V_{OUT} = 4.5 \text{ V}$)					
V_{OUT} Output voltage			4.5		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output voltage noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		13.5		μV_{PP}
REF5050 ($V_{OUT} = 5 \text{ V}$)					
V_{OUT} Output voltage			5		V
Initial accuracy, standard grade		-0.1%		0.1%	
Output voltage noise	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		15		μV_{PP}

(1) For $V_{OUT} \leq 2.5$ V, the minimum supply voltage is 2.7 V.

7.6 Electrical Characteristics: All Devices

Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to 125°C .

$T_A = 25^{\circ}\text{C}$, $I_{\text{LOAD}} = 0$, $C_L = 1\ \mu\text{F}$, $V_{\text{IN}} = (V_{\text{OUT}} + 0.2\ \text{V})$ to $18\ \text{V}$ (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
dV_{OUT}/dT	Output voltage temperature drift, standard grade	Over temperature		3	8	ppm/ $^{\circ}\text{C}$
$dV_{\text{OUT}}/dV_{\text{IN}}$	Line regulation	REF5020 only ⁽¹⁾	$V_{\text{IN}} = 2.7\ \text{V}$ to $18\ \text{V}$	0.1	1	ppm/V
		All other devices	$V_{\text{IN}} = V_{\text{OUT}} + 0.2\ \text{V}$	0.1	1	ppm/V
		All devices	Over temperature	0.2	1	ppm/V
$dV_{\text{OUT}}/dI_{\text{LOAD}}$	Load regulation	REF5020 only	$-10\ \text{mA} < I_{\text{LOAD}} < +10\ \text{mA}$, $V_{\text{IN}} = 3\ \text{V}$	20	30	ppm/mA
		All other devices	$-10\ \text{mA} < I_{\text{LOAD}} < +10\ \text{mA}$, $V_{\text{IN}} = V_{\text{OUT}} + 0.75\ \text{V}$	20	30	ppm/mA
		All devices	Over temperature, $-10\ \text{mA} < I_{\text{LOAD}} < +10\ \text{mA}$		50	ppm/mA
I_{SC}	Short-circuit current	$V_{\text{OUT}} = 0\ \text{V}$		25		mA
	Thermal hysteresis, ⁽²⁾ standard grade	Cycle 1		10		ppm
		Cycle 2		5		ppm
	Long-Term Stability	0 to 1000 hours		90		ppm/1000 hr
		1000 to 2000 hours		10		ppm/1000 hr
	Voltage output, TEMP pin	At $T_A = 25^{\circ}\text{C}$		575		mV
	Temperature sensitivity, TEMP pin	Over temperature		2.64		mV/ $^{\circ}\text{C}$
	Turn-on settling time	To 0.1% with $C_L = 1\ \mu\text{F}$		200		μs
V_S	Power supply voltage	See Note ⁽¹⁾	$V_{\text{OUT}} + 0.2$ ⁽¹⁾		18	V
	Power supply, quiescent current			0.8	1	mA
		Over temperature			1.2	mA
TEMPERATURE RANGE						
	Specified range		-40		125	$^{\circ}\text{C}$
	Operating range		-55		125	$^{\circ}\text{C}$
	Thermal resistance			150		$^{\circ}\text{C}/\text{W}$

(1) For $V_{\text{OUT}} \leq 2.5\ \text{V}$, the minimal supply voltage is $2.7\ \text{V}$.

(2) The [Thermal Hysteresis](#) section explains the thermal hysteresis procedure in detail.

7.7 Typical Characteristics

$T_A = 25^\circ\text{C}$, $I_{\text{LOAD}} = 0$, $V_S = V_{\text{OUT}} + 0.2\text{ V}$ (unless otherwise noted). For $V_{\text{OUT}} \leq 2.5\text{ V}$, the minimum supply voltage is 2.7 V.

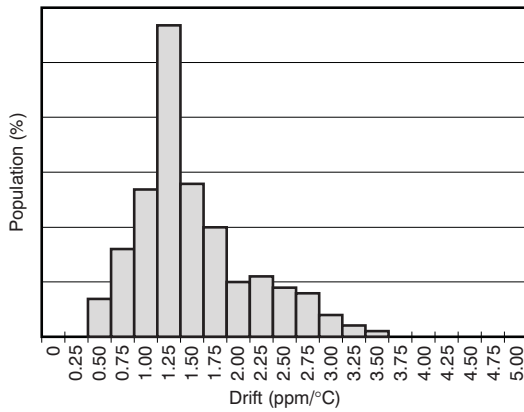


Figure 1. Temperature Drift (0°C to 85°C)

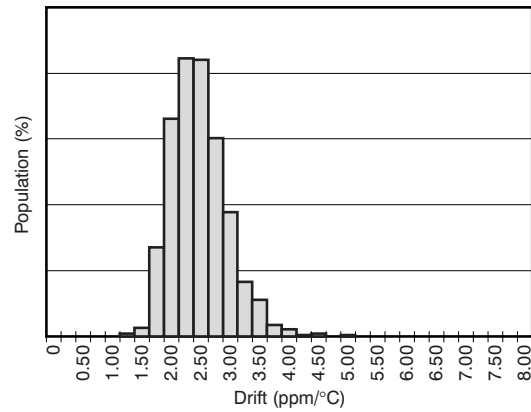


Figure 2. Temperature Drift (-40°C to 125°C)

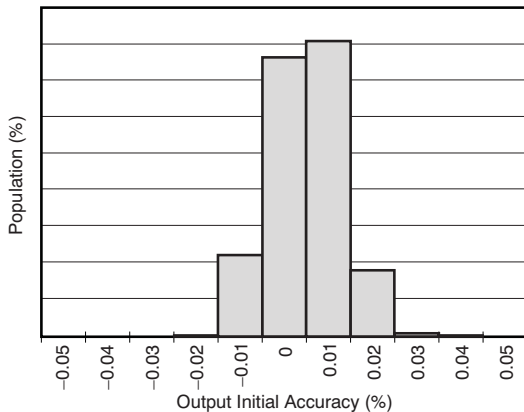


Figure 3. Output Voltage Initial Accuracy

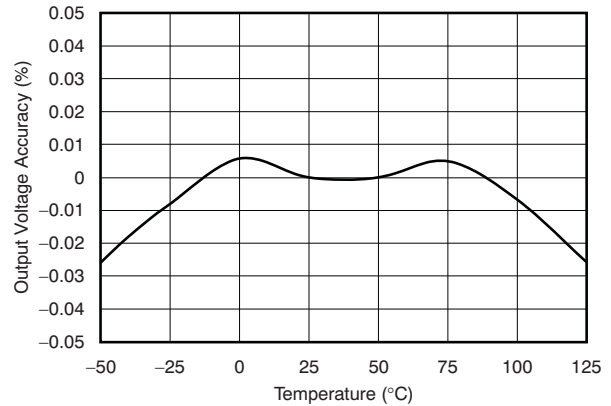


Figure 4. Output Voltage Accuracy vs Temperature

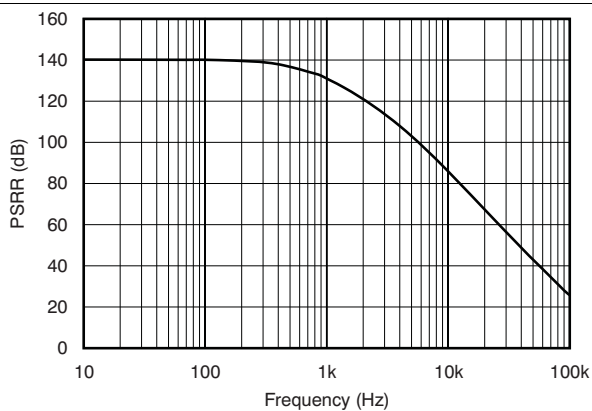


Figure 5. Power-Supply Rejection Ratio vs Frequency

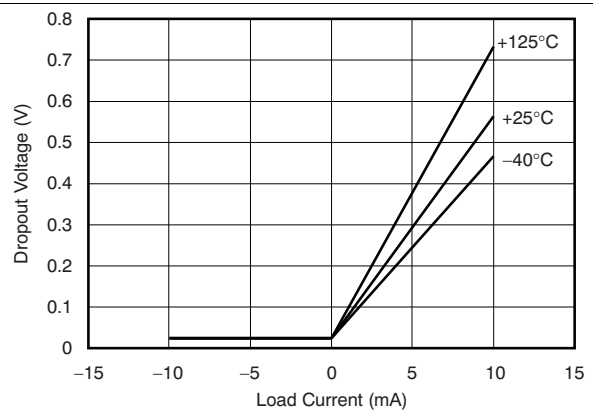


Figure 6. Dropout Voltage vs Load Current

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $I_{\text{LOAD}} = 0$, $V_S = V_{\text{OUT}} + 0.2\text{ V}$ (unless otherwise noted). For $V_{\text{OUT}} \leq 2.5\text{ V}$, the minimum supply voltage is 2.7 V.

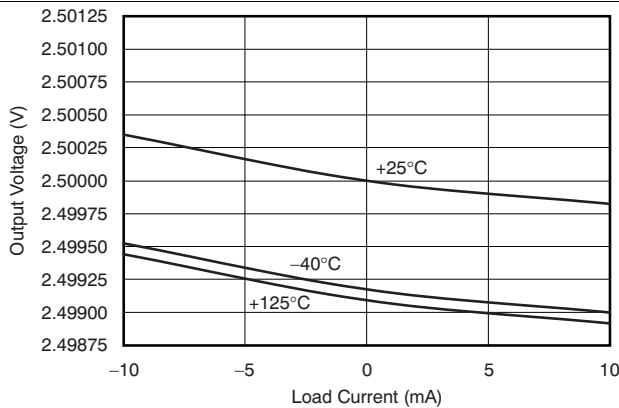


Figure 7. REF5025A-Q1 Output Voltage vs Load Current

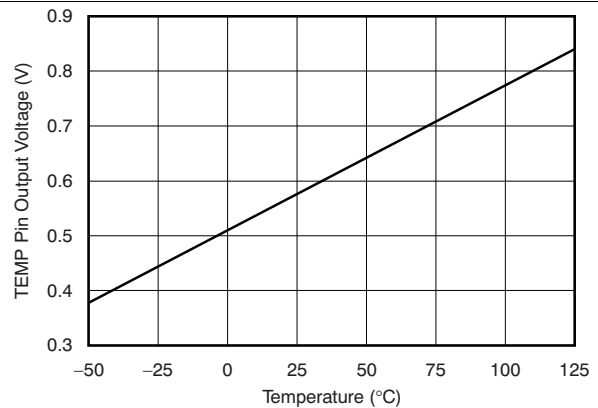


Figure 8. TEMP Pin Output Voltage vs Temperature

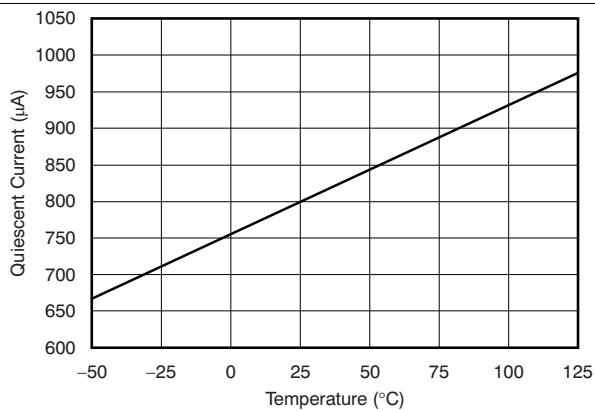


Figure 9. Quiescent Current vs Temperature

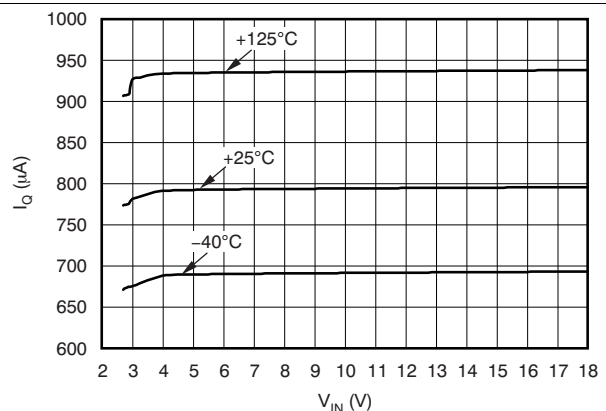


Figure 10. Quiescent Current vs Input Voltage

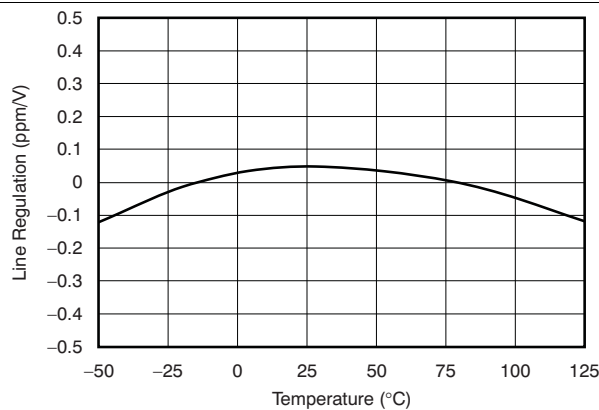


Figure 11. Line Regulation vs Temperature

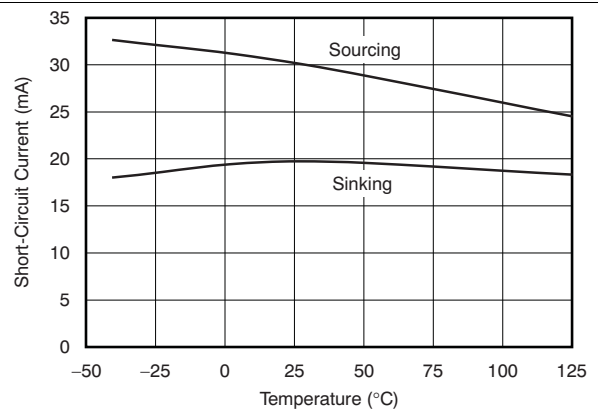


Figure 12. Short-Circuit Current vs Temperature

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $I_{\text{LOAD}} = 0$, $V_S = V_{\text{OUT}} + 0.2\text{ V}$ (unless otherwise noted). For $V_{\text{OUT}} \leq 2.5\text{ V}$, the minimum supply voltage is 2.7 V.

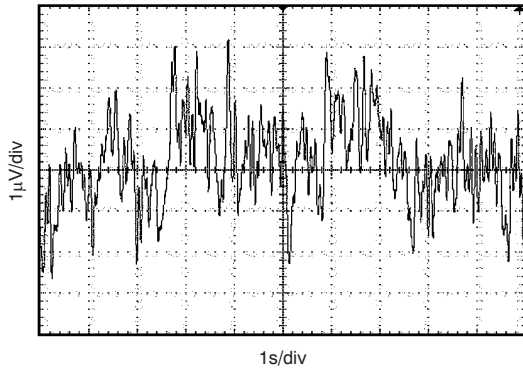


Figure 13. Noise

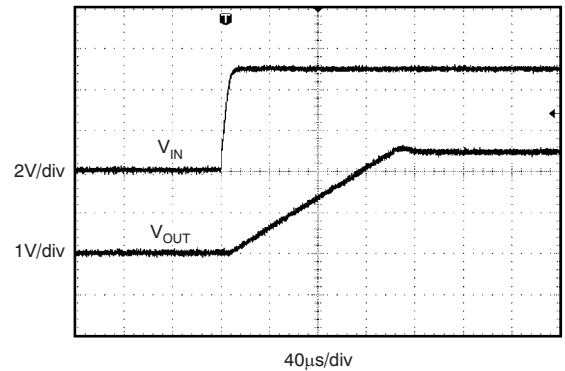


Figure 14. Startup (REF5025A-Q1, $C_L = 1\ \mu\text{F}$)

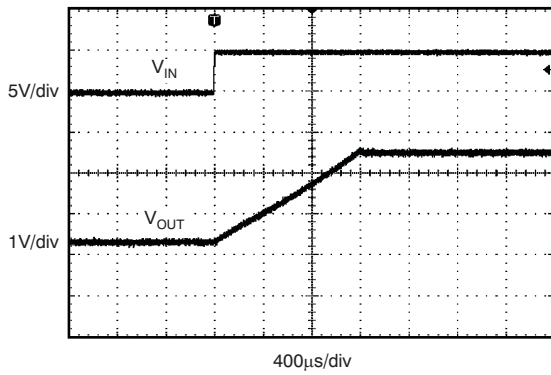


Figure 15. Startup (REF5025A-Q1, $C_L = 10\ \mu\text{F}$)

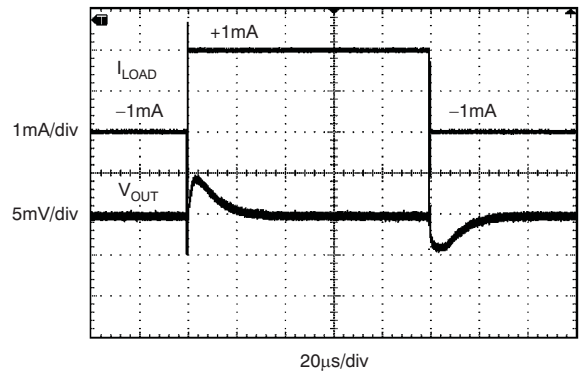


Figure 16. Load Transient ($C_L = 1\ \mu\text{F}$, $I_{\text{OUT}} = 1\text{ mA}$)

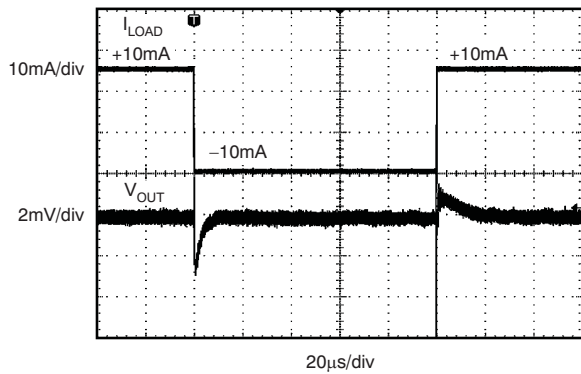


Figure 17. Load Transient ($C_L = 1\ \mu\text{F}$, $I_{\text{OUT}} = 10\text{ mA}$)

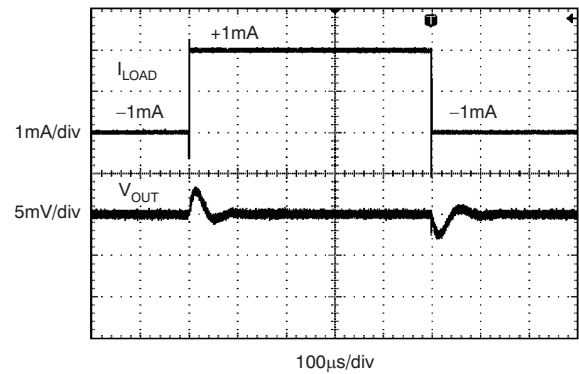


Figure 18. Load Transient ($C_L = 10\ \mu\text{F}$, $I_{\text{OUT}} = 1\text{ mA}$)

Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$, $I_{\text{LOAD}} = 0$, $V_S = V_{\text{OUT}} + 0.2\text{ V}$ (unless otherwise noted). For $V_{\text{OUT}} \leq 2.5\text{ V}$, the minimum supply voltage is 2.7 V.

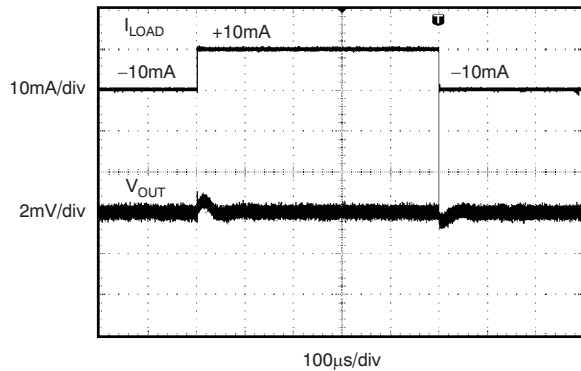


Figure 19. Load Transient ($C_L = 10\ \mu\text{F}$, $I_{\text{OUT}} = 10\ \text{mA}$)

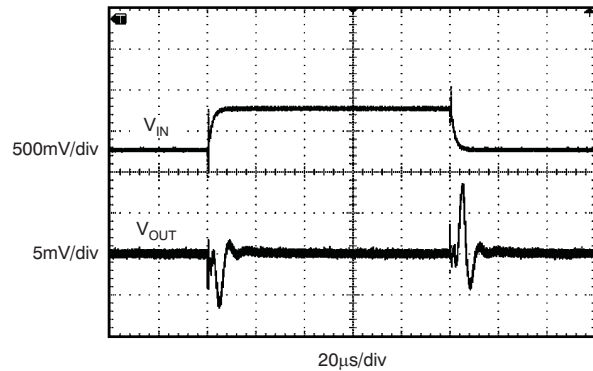


Figure 20. Line Transient ($C_L = 1\ \mu\text{F}$)

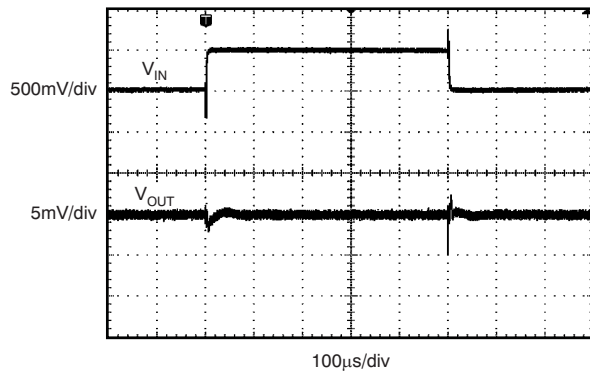


Figure 21. Line Transient ($C_L = 10\ \mu\text{F}$)

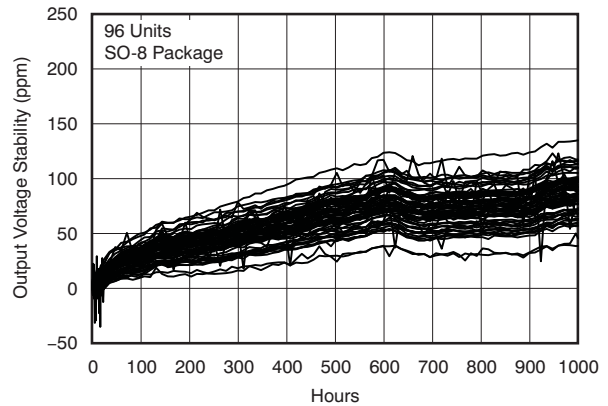


Figure 22. REF50xxA-Q1 Long-Term Stability (First 1000 Hours)

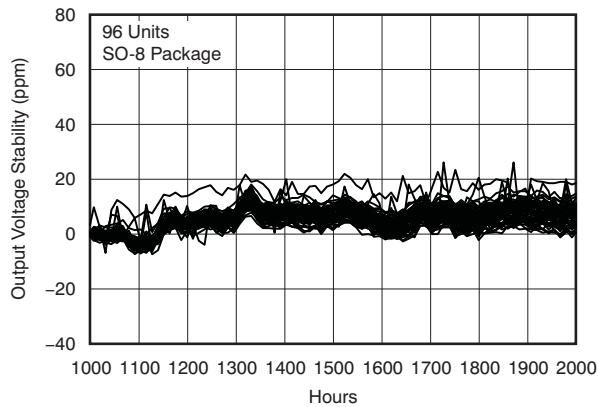


Figure 23. REF50xxA-Q1 Long-Term Stability (Second 1000 Hours)

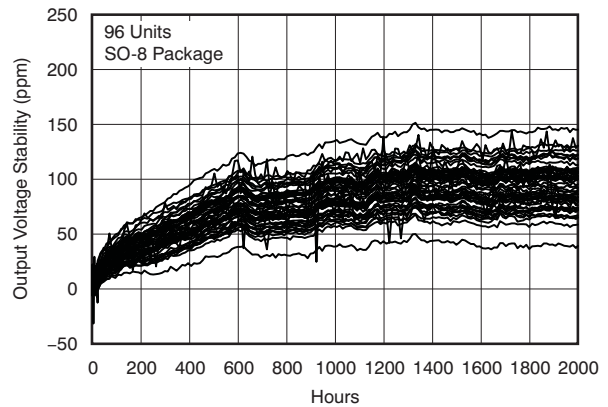


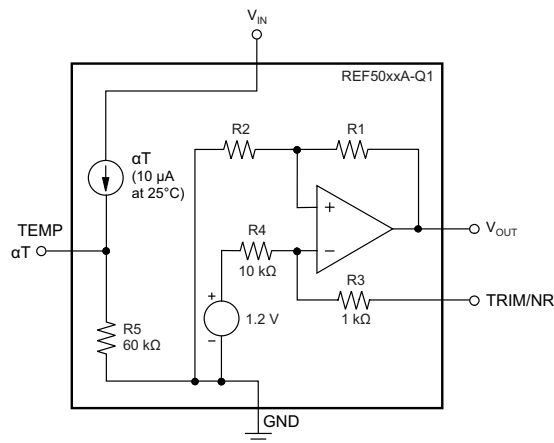
Figure 24. REF50xxA-Q1 Long-Term Stability (2000 Hours)

8 Detailed Description

8.1 Overview

The REF50xxA-Q1 family of devices is a low-noise, precision-bandgap voltage reference that is specifically designed for excellent initial voltage accuracy and drift. See the [Functional Block Diagram](#) section for a simplified block diagram of the REF50xxA-Q1 family of devices.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Supply Voltage

The REF50xxA-Q1 family of voltage references features extremely low dropout voltage. With the exception of the REF5020A-Q1 device, which has a minimum supply requirement of 2.7 V, these references can operate with a supply of 200 mV above the output voltage in an unloaded condition. For loaded conditions, [Figure 6](#) in the [Typical Characteristics](#) section shows a typical dropout voltage versus load plot.

8.3.2 Using the TRIM/NR Pin

The REF50xxA-Q1 family of devices provides a very accurate voltage output. However, V_{OUT} can be adjusted to reduce noise and shift the output voltage from the nominal value by configuring the trim and noise reduction pin (TRIM/NR, pin 5). The TRIM/NR pin provides a ± 15 -mV adjustment of the device bandgap, which produces a ± 15 -mV change on the V_{OUT} pin. [Figure 25](#) shows a typical circuit using the TRIM/NR pin to adjust V_{OUT} . When using this technique, the temperature coefficients of the resistors can degrade the temperature drift at the output.

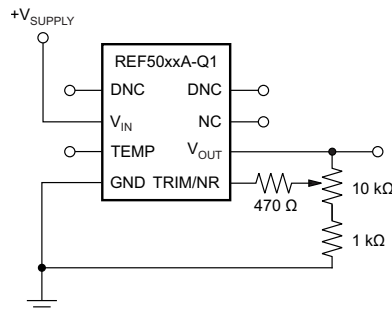


Figure 25. V_{OUT} Adjustment Using TRIM/NR Pin

Feature Description (continued)

The REF50xxA-Q1 family of devices allows access to the bandgap through the TRIM/NR pin. Placing a capacitor from the TRIM/NR pin to GND (as shown in [Figure 26](#)) in combination with the internal 1-kΩ resistor creates a low-pass filter that lowers the overall noise measured on the V_{OUT} pin. A capacitance of 1 μF is suggested for a low-pass filter with a corner frequency of 14.5 Hz. Higher capacitance results in a lower cutoff frequency.

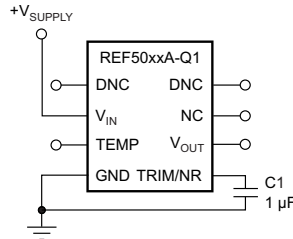


Figure 26. Noise Reduction Using TRIM/NR Pin

8.3.3 Temperature Drift

The REF50xxA-Q1 family of devices is designed for minimal drift error, which is defined as the change in output voltage over temperature. The drift is calculated using the box method. Use [Equation 1](#) to calculate the drift.

$$\text{Drift} = \left(\frac{V_{\text{OUTMAX}} - V_{\text{OUTMIN}}}{V_{\text{OUT}} \times \text{Temp Range}} \right) \times 10^6 (\text{ppm}) \quad (1)$$

The REF50xxA-Q1 family of devices features a maximum drift coefficient of 8 ppm/°C for the standard-grade.

8.3.4 Temperature Monitoring

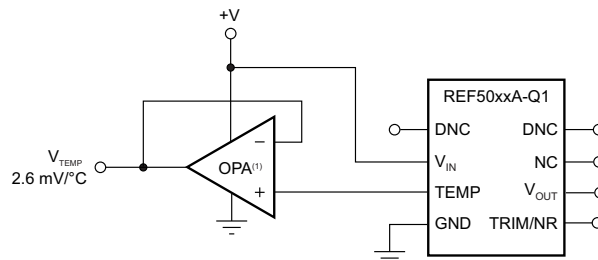
The temperature output pin (TEMP, pin 3) provides a temperature-dependent voltage output with approximately 60-kΩ source impedance. As shown in [Figure 8](#), the output voltage follows the nominal relationship:

$$V_{\text{TEMP PIN}} = 509 \text{ mV} + 2.64 \times T(^{\circ}\text{C}) \quad (2)$$

This pin indicates general chip temperature, accurate to approximately ±15°C. Although this pin is not generally suitable for accurate temperature measurements, it can be used to indicate temperature changes or for temperature compensation of analog circuitry. A temperature change of 30°C corresponds to an approximate 79-mV change in voltage at the TEMP pin.

The TEMP pin has high output impedance (see the [Functional Block Diagram](#) section). Loading this pin with a low-impedance circuit induces a measurement error; however, it does not have any effect on V_{OUT} accuracy.

To avoid errors caused by low-impedance loading, buffer the TEMP pin output with a suitable low-temperature drift op amp, such as the [OPA333](#), [OPA335](#), or [OPA376](#), as shown in [Figure 27](#).



(1) Low drift op amp, such as the OPA333, OPA335, or OPA376 device.

Figure 27. Buffering the TEMP Pin Output

8.4 Device Functional Modes

The REF50xxA-Q1 family of devices can only operate in an on or off mode. As long as a sufficient input supply voltage is made available to device, the device performs in standard operation. The device cannot be placed in a low power or shutdown mode.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Thermal Hysteresis

Thermal hysteresis for the REF50xxA-Q1 family of devices is defined as the change in output voltage after operating the device at 25°C, cycling the device through the specified temperature range, and returning to 25°C. Use Equation 3 to calculate the thermal hysteresis.

$$V_{\text{HYST}} = \left(\frac{|V_{\text{PRE}} - V_{\text{POST}}|}{V_{\text{NOM}}} \right) \cdot 10^6 \text{ (ppm)}$$

where

- V_{HYST} = thermal hysteresis (in units of ppm)
- V_{NOM} = the specified output voltage
- V_{PRE} = output voltage measured at 25°C pretemperature cycling
- V_{POST} = output voltage measured after the device has been cycled from 25°C through the specified temperature range of –40°C to +125°C and returned to 25°C

(3)

9.2 Typical Applications

9.2.1 Standalone Applications

Figure 28 shows the typical connections for the REF50xxA-Q1 family of devices.

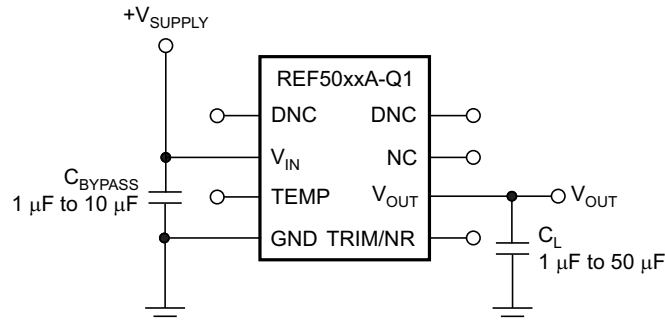


Figure 28. Basic Connections

Typical Applications (continued)

9.2.1.1 Design Requirements

A supply bypass capacitor with a value between 1 μF to 10 μF is recommended. A 1- μF to 50- μF , low-ESR output capacitor (C_L) must be connected from V_{OUT} to GND. The ESR value should be less than or equal to 1.5 Ω . The ESR minimizes gain peaking of the internal 1.2-V reference and thus reduces noise at the V_{OUT} pin.

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Power Dissipation

The REF50xxA-Q1 family of devices is specified to deliver current loads of ± 10 mA over the specified input voltage range. The temperature of the device increases according [Equation 4](#).

$$T_J = T_A + P_D \times R_{\theta JA}$$

where

- T_J = Junction temperature ($^{\circ}\text{C}$)
 - T_A = Ambient temperature ($^{\circ}\text{C}$)
 - P_D = Power dissipated (W)
 - $R_{\theta JA}$ = Junction-to-ambient thermal resistance ($^{\circ}\text{C}/\text{W}$)
- (4)

The junction temperature of the REF50xxA-Q1 family of devices must not exceed the absolute maximum rating of 150 $^{\circ}\text{C}$.

9.2.1.2.2 Noise Performance

The [Electrical Characteristics: Per Device](#) section specifies the typical voltage noise at 0.1 Hz to 10 Hz for each member of the REF50xxA-Q1 family of devices. The noise voltage increases with output voltage and operating temperature. Additional filtering can be used to improve output noise levels, although care should be taken to ensure the output impedance does not degrade performance.

For additional information about how to minimize noise and maximize performance in mixed-signal applications, such as data converters, refer to the series of *Analog Applications Journal* articles entitled, *How a Voltage Reference Affects ADC Performance*. See the [Related Documentation](#) section for a list of these articles.

9.2.1.3 Application Curves

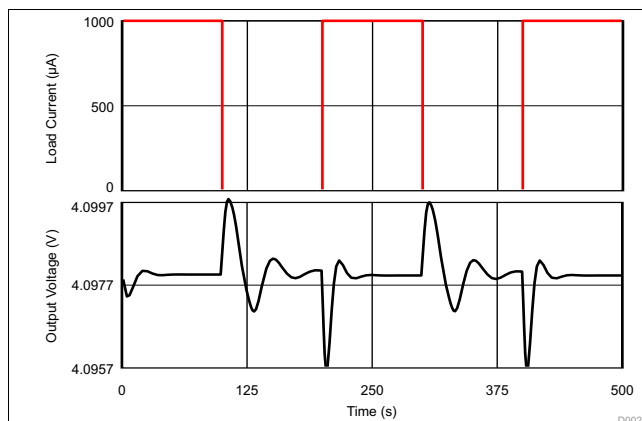


Figure 29. Transient Behavior of V_{OUT}

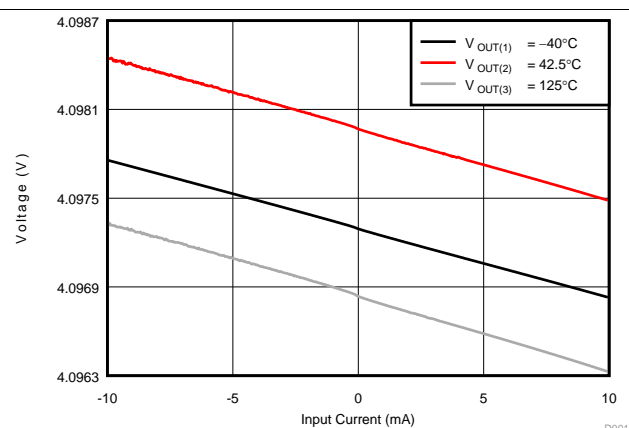
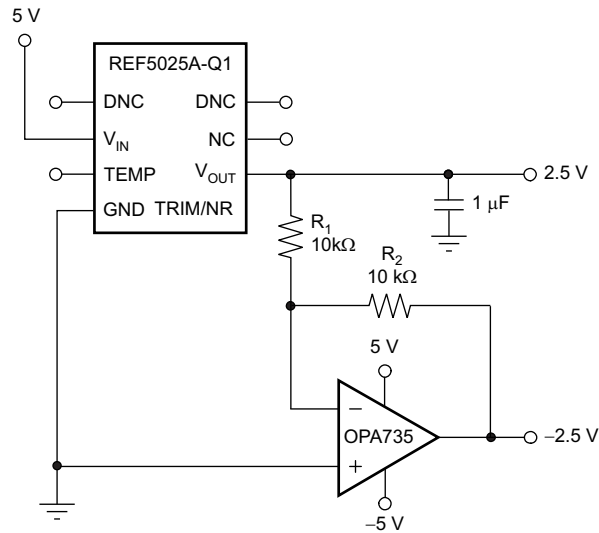


Figure 30. DC Analysis of V_{OUT} Across Various Temperatures and the Full Output-Current Range

Typical Applications (continued)

9.2.2 Negative-Reference Voltage Applications

For applications requiring a negative and positive reference voltage, the REF50xxA-Q1 family of devices and the OPA735 device can be used to provide a dual-supply reference from a 5-V supply. Figure 31 shows the REF5025A-Q1 used to provide a 2.5-V supply reference voltage. The low drift performance of the REF50xxA-Q1 family of devices complements the low offset voltage and zero drift of the OPA735 device to provide an accurate solution for split-supply applications. Care must be taken to match the temperature coefficients of R_1 and R_2 .



NOTE: Bypass capacitors not shown.

Figure 31. The REF5025A-Q1 and OPA735 Create Positive and Negative Reference Voltages

9.2.3 Data-Acquisition Applications

Data acquisition systems often require stable voltage references to maintain accuracy. The REF50xxA-Q1 family of devices features low noise, very low drift, and high initial accuracy for high-performance data converters. Figure 32 shows the REF5040A-Q1 in a basic data acquisition system.

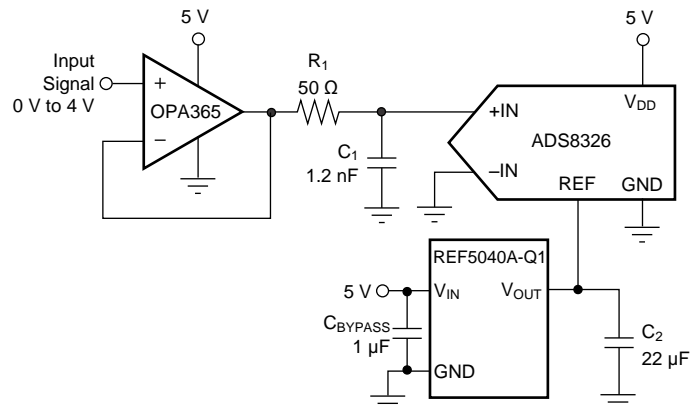


Figure 32. Basic Data Acquisition System

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- [ADS8326 16-Bit, High-Speed, 2.7V to 5.5V microPower Sampling ANALOG-TO-DIGITAL CONVERTER, SBAS343](#)
- *Analog Applications Journal—How a Voltage Reference Affects ADC Performance:*
 - Part 1, [SLYT331](#)
 - Part 2, [SLYT339](#)
 - Part 3, [SLYT355](#)
- [OPA333 1.8-V, microPower, CMOS Operational Amplifiers, Zero-Drift Series, SBOS351](#)
- [OPA333-Q1 1.8-V MICROPOWER CMOS OPERATIONAL AMPLIFIER ZERO-DRIFT SERIES, SBOS522](#)
- [OPA335 0.05µV/°C max, SINGLE-SUPPLY CMOS OPERATIONAL AMPLIFIERS Zero-Drift Series, SBOS245](#)
- [OPA365 50MHz, Low-Distortion, High CMRR, RRI/O, Single-Supply OPERATIONAL AMPLIFIER, SBOS365](#)
- [OPA365-Q1 50-MHz Low-Distortion High-CMRR Rail-to-Rail I/O, Single-Supply Operational Amplifier, SBOS512](#)
- [OPA376 Low-Noise, Low Quiescent Current, Precision Operational Amplifier e-trim™ Series, SBOS406](#)
- [OPA376-Q1 Low-Noise, Low Quiescent Current, Precision Operational Amplifier e-trim™ Series, SBOS549](#)
- [OPA735 0.05µV/°C max, SINGLE-SUPPLY CMOS OPERATIONAL AMPLIFIERS Zero-Drift Series, SBOS282](#)

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
REF5020A-Q1	Click here	Click here	Click here	Click here	Click here
REF5025A-Q1	Click here	Click here	Click here	Click here	Click here
REF5030A-Q1	Click here	Click here	Click here	Click here	Click here
REF5040A-Q1	Click here	Click here	Click here	Click here	Click here
REF5045A-Q1	Click here	Click here	Click here	Click here	Click here
REF5050A-Q1	Click here	Click here	Click here	Click here	Click here

12.3 Trademarks

All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
REF5020AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5020 A	Samples
REF5025AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5025 A	Samples
REF5030AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5030 A	Samples
REF5040AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5040 A	Samples
REF5045AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5045 A	Samples
REF5050AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RFQ 5050 A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
REF5020AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
REF5025AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
REF5030AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
REF5040AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
REF5045AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
REF5050AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
REF5020AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
REF5025AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
REF5030AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
REF5040AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
REF5045AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0
REF5050AQDRQ1	SOIC	D	8	2500	356.0	356.0	35.0



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

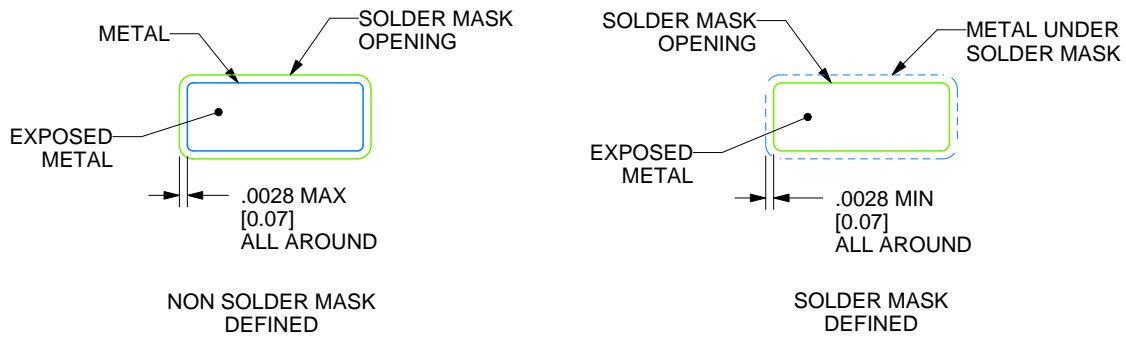
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2022, Texas Instruments Incorporated

单击下面可查看定价，库存，交付和生命周期等信息

[>>TI\(德州仪器\)](#)